MICRO ELECTRONICS

2SB621,A
2SD592,A

SILICON TRANSISTORS

TO-92

ECB

2SB621,A (PNP) & 2SD592,A (NPN) are complementary silicon planar epitaxial transistors designed for AF output amplifiers.

ABSOLUTE MAXIMUM RATINGS

		2SD592 / 2SB621	2SD592A / 2SB621A
Collector-Base Voltage	VCBO	30V	60V
Collector-Emitter Voltage	VCEO	25V	50V
Emittter-Base Voltage	VEBO	5V	
Collector Current	IC	1A	
Total Power Dissipation	Ptot	750mW	
Operating Junction & Storage Temperature	Tj,Tstg	-55 to +150°C	

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITION
Collector Cutoff Current	ICBO		100	nA	VCB=20V IE=0
Collector-Base Breakdown Voltage 2SB621 /2SD592	BVCBO	30		V	IC=10μA IE=0
2SB621A/2SD592A		60			
Collector-Emitter Breakdown Voltage 2SB621 /2SD592	LVCEO	25		V	IC=2mA IB=0
2SB621A/2SD592A		50			
Emitter-Base Breakdown Voltage	BVEBO	5		V	IE=10μA IC=0
D.C. Current Gain	HFE	85	340		IC=500mA VCE=10V*
		50			IC=1A VCE=10V*
Collector-Emitter Saturation Voltage	VCE(sat)		0.4	V	IC=500mA IB=50mA*
Base-Emitter Saturation Voltage	VBE(sat)		1.2	V	IC=500mA IB=50mA*
Current Gain Bandwidth Product	fT	200 TYP		MHz	IC=50mA VCE=10V
Output Capacitance 2SB621,A	Cob		30	pF	VCB=10V f=1MHz
2SD592,A			20	pF	

Pulse Test : Pulse Width < 300uS, Duty Cycle < 1%.

HFE Grouping

Q : 85-170 R : 120-240 S : 170-340

MICRO ELECTRONICS LTD. 美科有限公司 FAX: 3-410321
38 Hung To Road, Kwun Tong, Kowloon, Hong Kong. Cable: Microtron, Hong Kong. Telex: 43510 Micro Hx.
P.O. Box 9477, Kwun Tong. Tel: 3-430181-6, ~~3-893363, 3-892423, 3-898221~~

1-1.0mp